

## Low drop power Schottky rectifier

### Main product characteristics

$I_{F(AV)}$	2 x 10 A
$V_{RRM}$	45 V
$T_j$ (max)	150° C
$V_F$ (max)	0.5 V

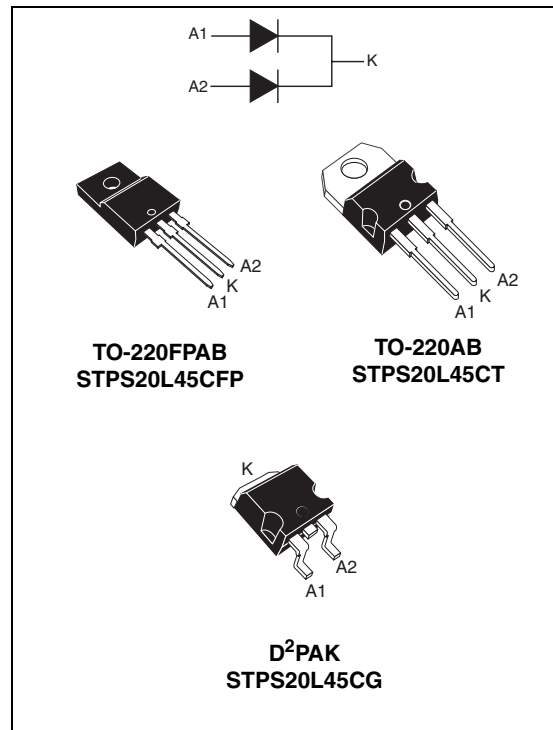
### Features and benefits

- Low forward voltage drop meaning very small conduction losses
- Low switching losses allowing high frequency operation
- Insulated package: TO-220FPAB  
Insulating voltage = 2000 V DC  
Capacitance = 12 pF
- Avalanche capability specified

### Description

Dual center tap Schottky rectifiers designed for high frequency switched mode power supplies and DC to DC converters.

These devices are intended for use in low voltage, high frequency inverters, free-wheeling and polarity protection applications.



# 1 Characteristics

**Table 1. Absolute Ratings (limiting values)**

Symbol	Parameter			Value	Unit	
$V_{RRM}$	Repetitive peak reverse voltage			45	V	
$I_{F(RMS)}$	RMS forward voltage			30	A	
$I_{F(AV)}$	Average forward current	TO-220AB / D <sup>2</sup> PAK	$T_c = 135^\circ\text{C}$ $\delta = 0.5$	Per diode Per device	10 20	A
		TO-220FPAB	$T_c = 115^\circ\text{C}$ $\delta = 0.5$	Per diode Per device	10 20	A
$I_{FSM}$	Surge non repetitive forward current			$t_p = 10\text{ ms}$ Sinusoidal	180	A
$I_{RRM}$	Peak repetitive reverse current			$t_p = 2\ \mu\text{s}$ square F = 1 kHz	1	A
$I_{RSM}$	Non repetitive peak reverse current			$t_p = 100\ \mu\text{s}$ square	2	A
$P_{ARM}$	Repetitive peak avalanche power			$t_p = 1\ \mu\text{s}$ $T_j = 25^\circ\text{C}$	4000	W
$T_{stg}$	Storage temperature range			-65 to +150	$^\circ\text{C}$	
$T_j$	Maximum operating junction temperature <sup>(1)</sup>			150	$^\circ\text{C}$	
dV/dt	Critical rate of rise of reverse voltage			10000	V/ $\mu\text{s}$	

1.  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$  condition to avoid thermal runaway for a diode on its own heatsink

**Table 2. Thermal resistances**

Symbol	Parameter			Value	Unit
$R_{th(j-c)}$	Junction to case	TO-220FPAB	Per diode	4.5	$^\circ\text{C/W}$
			Total	3.5	
			Coupling	2.5	
$R_{th(j-c)}$	Junction to case	TO-220AB / D <sup>2</sup> PAK	Per diode	2.2	$^\circ\text{C/W}$
			Total	1.3	
			Coupling	0.3	

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

**Table 3. Static electrical characteristics (per diode)**

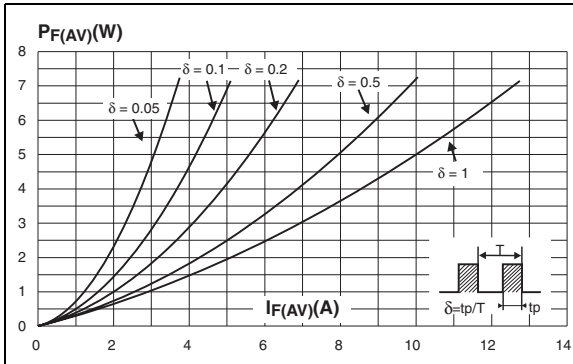
Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			0.2	mA
		$T_j = 125^\circ\text{C}$			65	130	mA
$V_F^{(1)}$	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 10\text{ A}$		0.44	0.55	V
		$T_j = 125^\circ\text{C}$	$I_F = 10\text{ A}$			0.5	
		$T_j = 25^\circ\text{C}$	$I_F = 20\text{ A}$			0.73	
		$T_j = 125^\circ\text{C}$	$I_F = 20\text{ A}$		0.62	0.72	

1. Pulse test:  $t_p = 380\ \mu\text{s}$ ,  $\delta < 2\%$

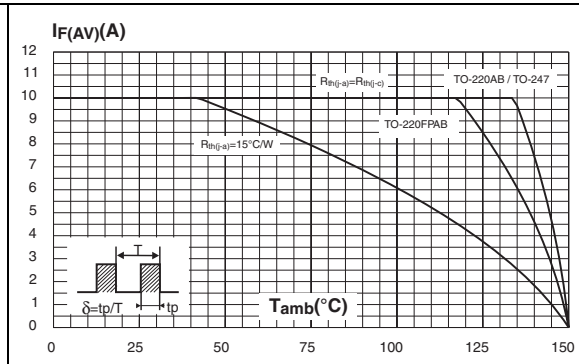
To evaluate the conduction losses use the following equation:

$$P = 0.28 \times I_{F(AV)} + 0.022 I_{F(RMS)}^2$$

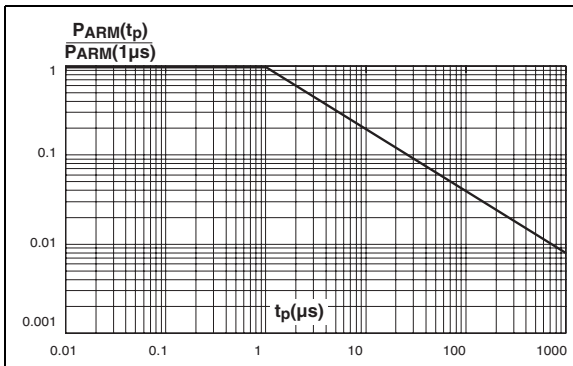
**Figure 1. Average forward power dissipation versus average forward current (per diode)**



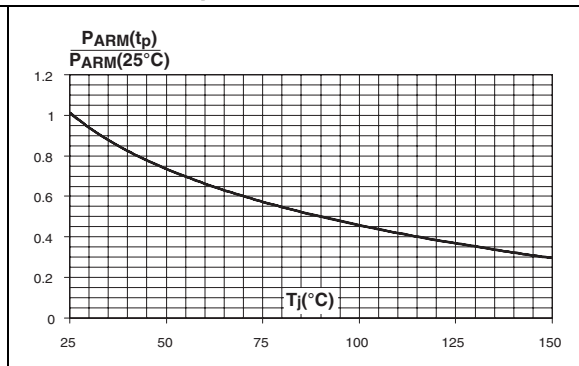
**Figure 2. Average forward current versus ambient temperature ( $\delta = 0.5$ , per diode)**



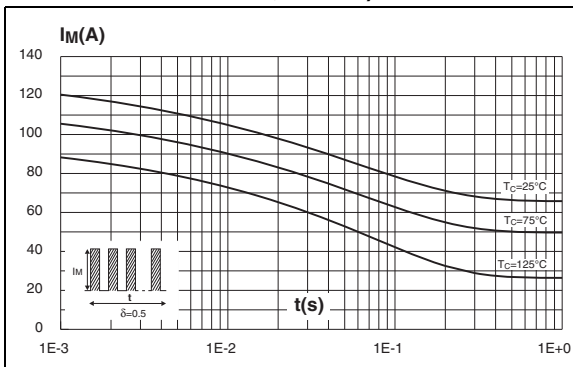
**Figure 3. Normalized avalanche power derating versus pulse duration**



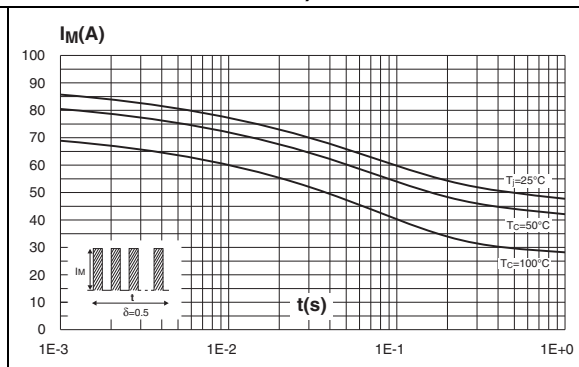
**Figure 4. Normalized avalanche power derating versus junction temperature**



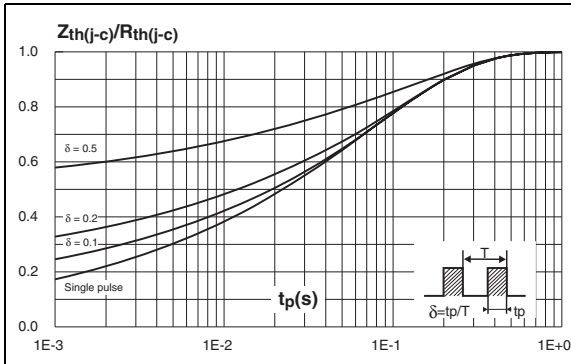
**Figure 5. Non repetitive surge peak forward current versus overload duration (maximum values, per diode, TO-220AB, D<sup>2</sup>PAK)**



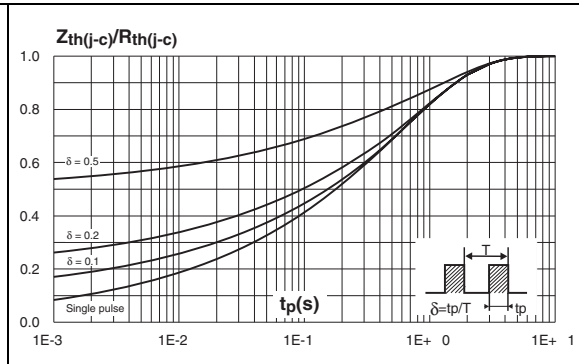
**Figure 6. Non repetitive surge peak forward current versus overload duration (maximum values, per diode, TO-220FPAB)**



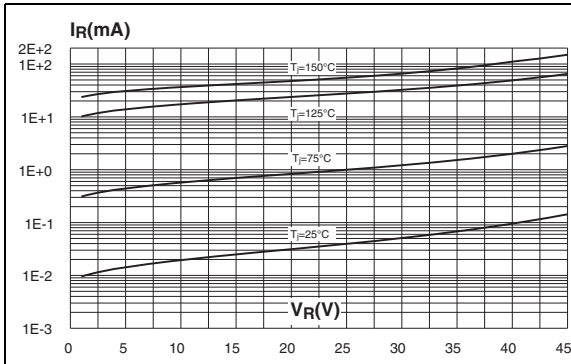
**Figure 7. Relative variation of thermal impedance junction to case versus pulse duration (TO-220AB, D<sup>2</sup>PAK)**



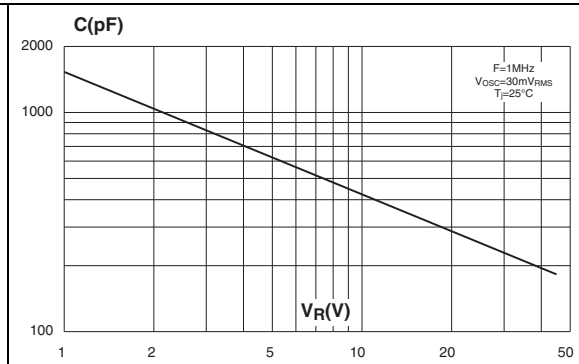
**Figure 8. Relative variation of thermal impedance junction to case versus pulse duration (TO-220FPAB)**



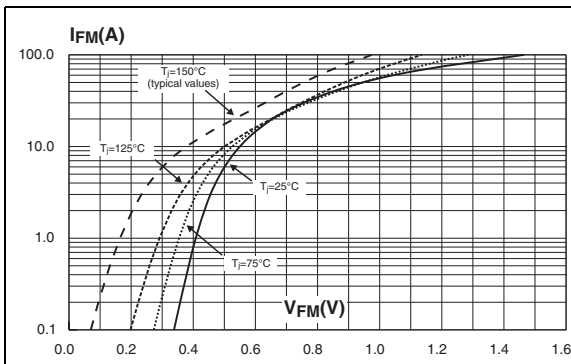
**Figure 9. Reverse leakage current versus reverse voltage applied (typical values, per diode)**



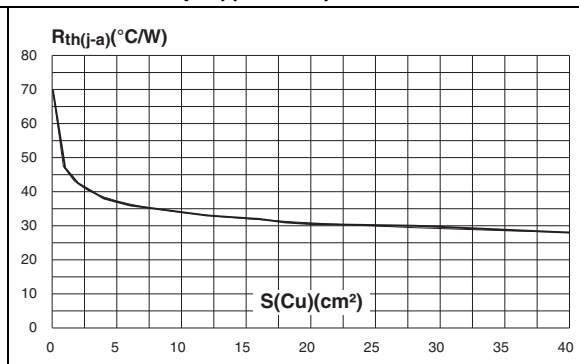
**Figure 10. Junction capacitance versus reverse voltage applied (typical values, per diode)**



**Figure 11. Forward voltage drop versus forward current (maximum values, per diode)**



**Figure 12. Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness: 35µm)( D<sup>2</sup>PAK)**



## 2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 Nm
- Maximum torque value: 0.70 Nm

Table 4. TO-220FPAB dimensions

Ref	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.4	4.6	0.173	0.181
B	2.5	2.7	0.098	0.106
D	2.5	2.75	0.098	0.108
E	0.45	0.70	0.018	0.027
F	0.75	1	0.030	0.039
F1	1.15	1.70	0.045	0.067
F2	1.15	1.70	0.045	0.067
G	4.95	5.20	0.195	0.205
G1	2.4	2.7	0.094	0.106
H	10	10.4	0.393	0.409
L2	16 Typ.		0.63 Typ.	
L3	28.6	30.6	1.126	1.205
L4	9.8	10.6	0.386	0.417
L5	2.9	3.6	0.114	0.142
L6	15.9	16.4	0.626	0.646
L7	9.00	9.30	0.354	0.366
Dia.	3.00	3.20	0.118	0.126

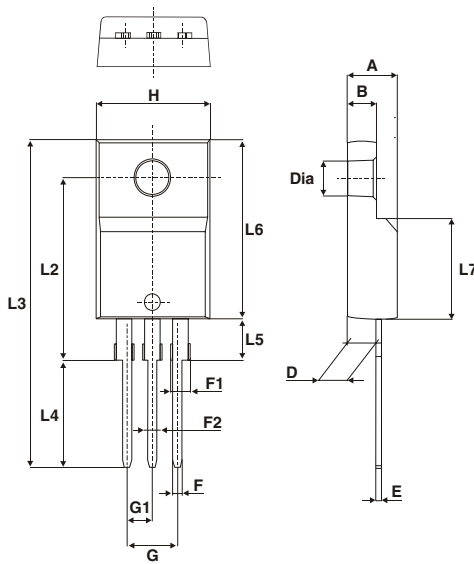
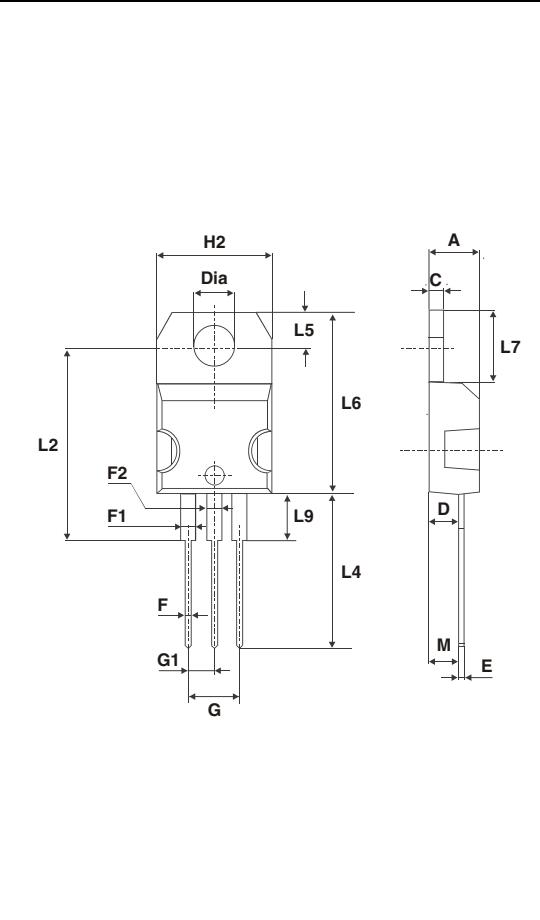


Table 5. TO-220AB dimensions

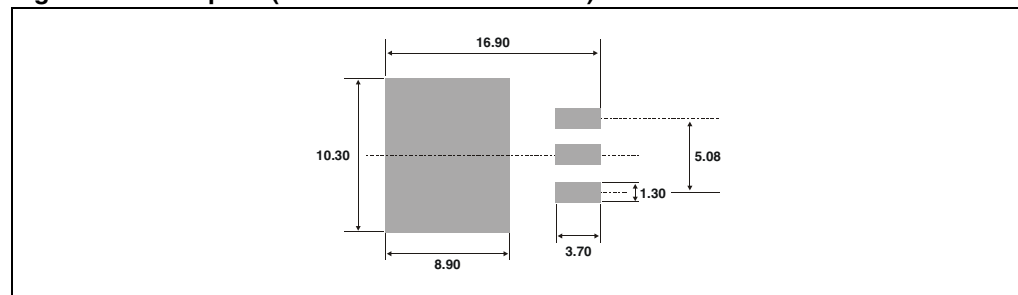


Ref	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
F2	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
G1	2.40	2.70	0.094	0.106
H2	10	10.40	0.393	0.409
L2	16.4 typ.		0.645 typ.	
L4	13	14	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
Diam.	3.75	3.85	0.147	0.151

Table 6. D<sup>2</sup>PAK dimensions

Ref	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.49	2.69	0.098	0.106
A2	0.03	0.23	0.001	0.009
B	0.70	0.93	0.027	0.037
B2	1.14	1.70	0.045	0.067
C	0.45	0.60	0.017	0.024
C2	1.23	1.36	0.048	0.054
D	8.95	9.35	0.352	0.368
E	10.00	10.40	0.393	0.409
G	4.88	5.28	0.192	0.208
L	15.00	15.85	0.590	0.624
L2	1.27	1.40	0.050	0.055
L3	1.40	1.75	0.055	0.069
M	2.40	3.20	0.094	0.126
R	0.40 typ.		0.016 typ.	
V2	0°	8°	0°	8°

Figure 13. Footprint (dimensions in millimeters)



In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com).

### 3 Ordering Information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS20L45CFP	STPS20L45CFP	TO-220FPAB	2 g	50	Tube
STPS20L45CT	STPS20L45CT	TO-220AB	2 g	50	Tube
STPS20L45CG	STPS20L45CG	D <sup>2</sup> PAK	1.48 g	50	Tube
STPS20L45CG-TR	STPS20L45CG	D <sup>2</sup> PAK	1.48 g	1000	Tape & Reel

### 4 Revision history

Date	Revision	Description of Changes
Jul_2003	3C	Last release.
22-Mar-2007	4	Removed ISOWATT and TO-247 packages.



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